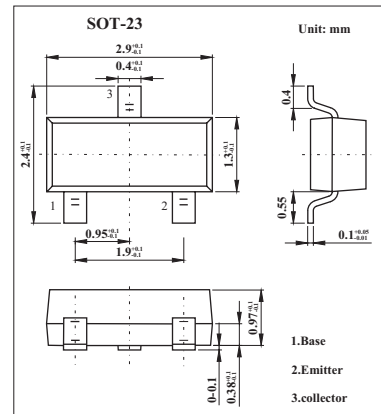


BCX17,BCX18

■ Features

- Low current (max. 100 mA).
- Low voltage (max. 32 V).



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	BCX17	BCX18	Unit
Collector-base voltage	V _{CB0}	-50	-30	V
Collector-emitter voltage	V _{CEO}	-45	-25	V
Emitter-base voltage	V _{EBO}	-5		V
Collector current	I _C	-500		mA
Peak collector current	I _{CM}	-1000		mA
Peak base current	I _{BM}	-200		mA
Total power dissipation *	P _{tot}	250		mW
Storage temperature	T _{stg}	-65 to +150		°C
Junction temperature	T _j	150		°C
Operating ambient temperature	R _{amb}	-65 to +150		°C
Thermal resistance from junction to ambient *	R _{th-j-a}	500		K/W

* Transistor mounted on an FR4 printed-circuit board.

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector cutoff current	I _{CBO}	I _E = 0; V _{CB} = -20 V			-100	nA
	I _{CBO}	I _E = 0; V _{CB} = -20 V; T _j = 100 °C			-5	µA
Emitter cutoff current	I _{EBO}	I _C = 0; V _{EB} = -5 V			-100	nA
DC current gain	h _{FE}	I _C = -100 mA; V _{CE} = -1 V	100		600	
		I _C = -300 mA; V _{CE} = -1 V	70			
		I _C = -500 mA; V _{CE} = -1 V	40			
Collector-emitter saturation voltage	V _{CE(sat)}	I _C = -500 mA; I _B = -50 mA			-620	mV
Base to emitter voltage	V _{BE}	I _C = -500 mA; V _{CE} = -1 V			-1.2	V
Collector capacitance	C _c	I _E = I _E = 0; V _{CB} = -10 V; f = 1 MHz		9		pF
Transition frequency	f _T	I _C = -10 mA; V _{CE} = -5 V; f = 100 MHz	80			MHz

■ hFE Classification

TYPE	BCX17	BCX18
Marking	T1	T2